

JUNCTION FIELD EFFECT TRANSISTOR 2SK1108

N-CHANNEL SILICON JUNCTION FIELD EFFECT TRANSISTOR FOR IMPEDANCE CONVERTER OF ECM

DESCRIPTION

The 2SK1108 is suitable for converter of ECM.

FEATURES

- · Compact package
- High forward transfer admittance 1000 μ S TYP. (lbss = 100 μ A) 1600 μ S TYP. (lbss = 200 μ A)
- Includes diode and high resistance at G S

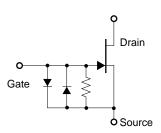
ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK1108	SST

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage Note	VDSX	20	V
Gate to Drain Voltage	V_{GDO}	-20	V
Drain Current	ΙD	10	mΑ
Gate Current	lg	10	mΑ
Total Power Dissipation	Рт	100	mW
Junction Temperature	Tj	125	°C
Storage Temperature	Tstg	-55 to +125	°C

EQUIVALENT CIRCUIT



Note Vgs = -1.0 V

Remark Please take care of ESD (Electro Static Discharge) when you handle the device in this document.

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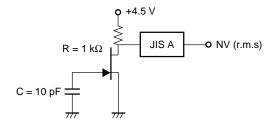
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.



ELECTRICAL CHARACTERISTICS (TA = 25°C)

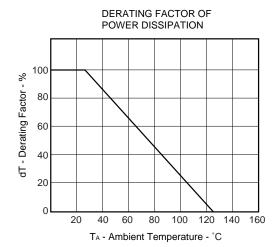
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Cut-off Current	IDSS	V _{DS} = 5.0 V, V _{GS} = 0 V	40		600	μΑ
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = 5.0 \text{ V}, I_{D} = 1.0 \mu \text{A}$	-0.1		-1.0	V
Forward Transfer Admittance	y fs1	$V_{DS} = 5.0 \text{ V}, \text{ ID} = 20 \ \mu\text{A}, \text{ f} = 1.0 \text{ kHz}$	350			μS
Forward Transfer Admittance	y fs2	V _{DS} = 5.0 V, V _{GS} = 0 V, f = 1.0 kHz	350			μS
Input Capacitance	Ciss	V _{DS} = 5.0 V, V _{GS} = 0 V, f = 1.0 kHz		7.0	8.0	pF
Noise Voltage	NV	See Test Circuit		1.8	3.0	μV

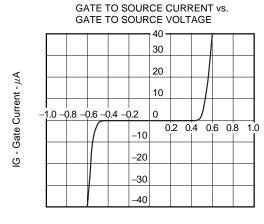
NOISE VOLTAGE TEST CIRCUIT



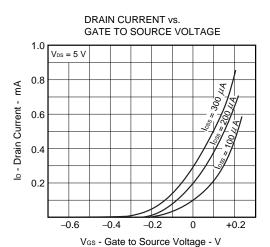


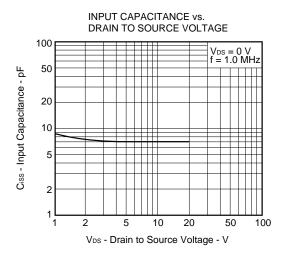
TYPICAL CHARACTERISTICS (TA = 25°C)



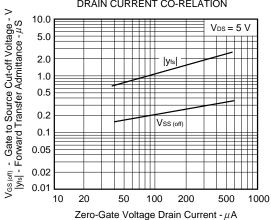


V_{GS} - Gate to Source Voltage - V

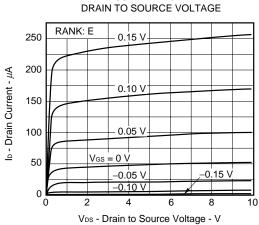




GATE TO SOURCE CUT-OFF VOLTAGE AND FORWARD TRANSFER ADMITTANCE vs. ZERO-GATE VOLTAGE DRAIN CURRENT CO-RELATION

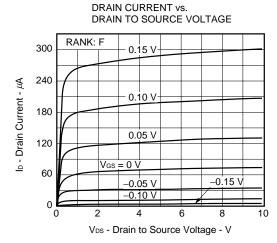


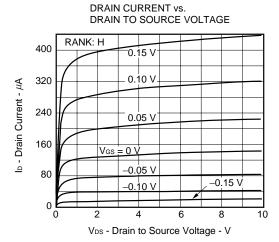
Data Sheet D15951EJ1V0DS 3

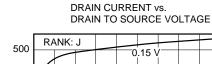


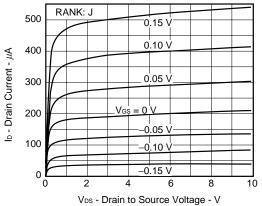
DRAIN CURRENT vs.

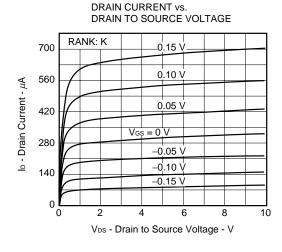


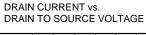


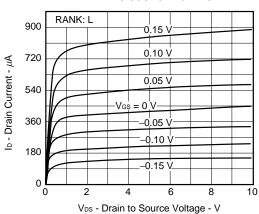




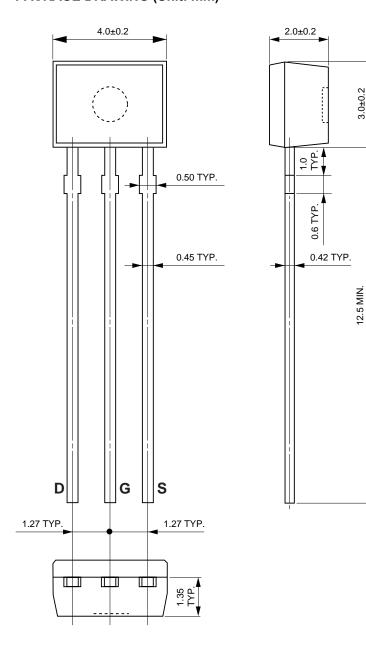








PACKAGE DRAWING (Unit: mm)



 3.0 ± 0.2

[MEMO]

[MEMO]

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